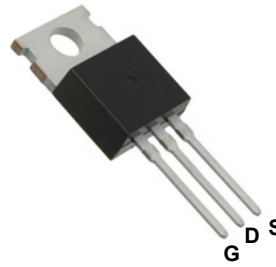
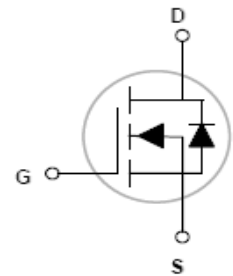


Main Product Characteristics

BV_{DSS}	100V
$R_{DS(ON)}$	3.7m Ω
I_D	150A



TO-220



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFH0980 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	+20/-12	V
Drain Current-Continuous(T _C =25°C)	I_D	150	A
Drain Current-Continuous(T _C =100°C)		95	A
Drain Current-Pulsed ¹	I_{DM}	600	A
Single Pulse Avalanche Energy ²	E_{AS}	378	mJ
Single Pulse Avalanche Current ²	I_{AS}	87	A
Power Dissipation(T _C =25°C)	P_D	275	W
Power Dissipation-Derate Above 25°C		2.22	W/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.45	°C/W
Storage Temperature Range	T_{STG}	-50 To +150	°C
Operating Junction Temperature Range	T_J	-50 To +150	°C

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V, T_J=25^\circ\text{C}$	-	-	1	μA
		$V_{DS}=80V, V_{GS}=0V, T_J=85^\circ\text{C}$	-	-	10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$	-	-	100	nA
On Characteristics						
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$	-	3.1	3.7	m Ω
		$V_{GS}=4.5V, I_D=15A$	-	4.5	6	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.8	2.5	V
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=3A$	-	20	-	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{3,4}	Q_g	$V_{DS}=80V, I_D=10A, V_{GS}=10V$	-	110	165	nC
Gate-Source Charge ^{3,4}	Q_{gs}		-	11.5	18	
Gate-Drain Charge ^{3,4}	Q_{gd}		-	28	42	
Turn-On Delay Time ^{3,4}	$t_{d(on)}$	$V_{DD}=50V, R_G=6\Omega, V_{GS}=10V, I_D=1A$	-	23	46	nS
Rise Time ^{3,4}	t_r		-	32	64	
Turn-Off Delay Time ^{3,4}	$t_{d(off)}$		-	157	320	
Fall Time ^{3,4}	t_f		-	115	230	
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, F=1\text{MHz}$	-	6680	13300	pF
Output Capacitance	C_{oss}		-	1690	3380	
Reverse Transfer Capacitance	C_{rss}		-	78	156	
Gate Resistance	R_g	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	-	1.9	-	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_S	$V_G=V_D=0V, \text{Force Current}$	-	-	150	A
Pulsed Source Current	I_{SM}		-	-	300	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	-	-	1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=87A, R_G=25\Omega$ Starting $T_J=25^\circ\text{C}$
3. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

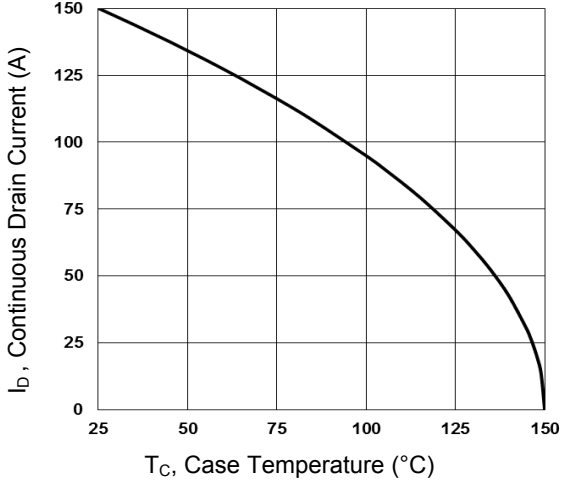


Figure 1. Continuous Drain Current vs. T_c

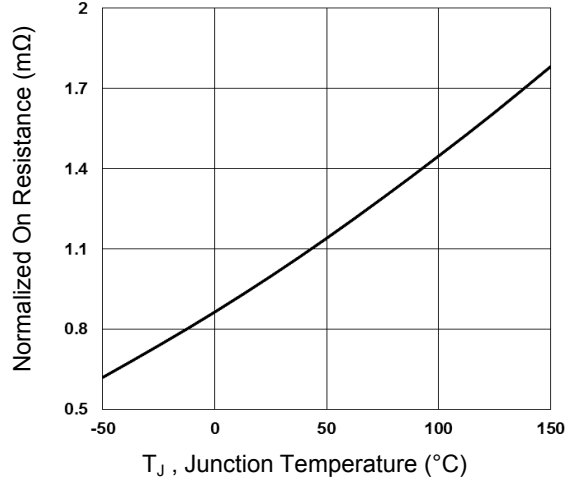


Figure 2. Normalized R_{DS(on)} vs. T_J

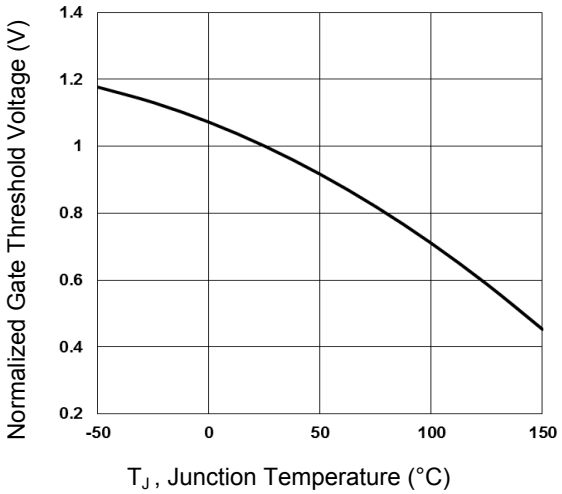


Figure 3. Normalized V_{th} vs. T_J

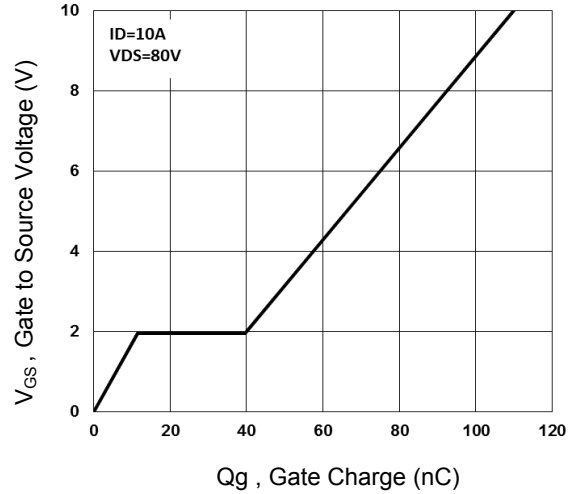


Figure 4. Gate Charge Characteristics

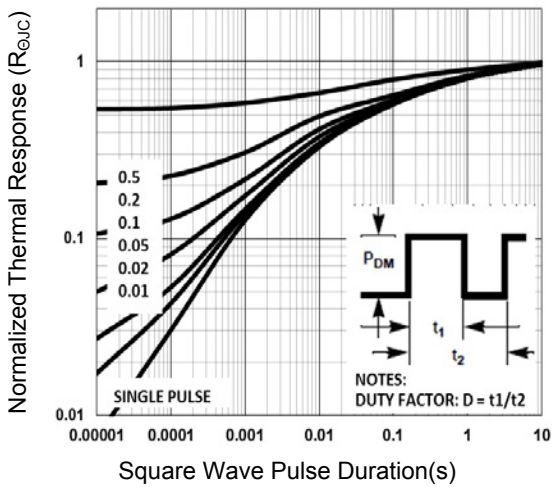


Figure 5. Normalized Transient Impedance

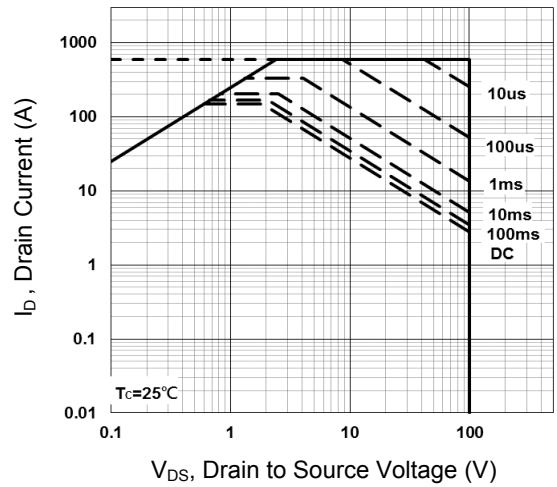


Figure 6. Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

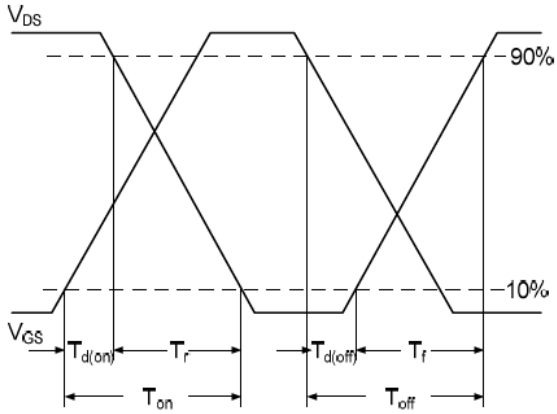


Figure 7. Switching Time Waveform

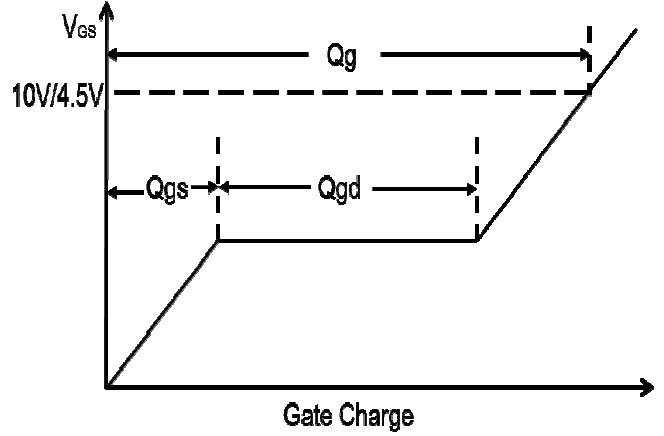
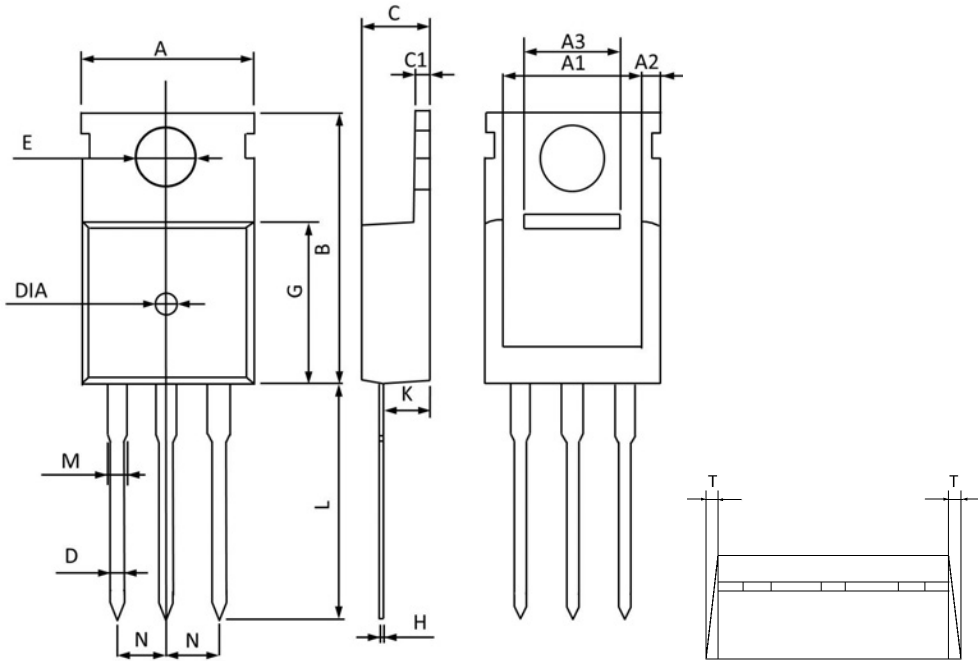


Figure 8. Gate Charge Waveform

Package Outline Dimensions (TO-220)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	10.300	9.700	0.406	0.382
A1	8.840	8.440	0.348	0.332
A2	1.250	1.050	0.049	0.041
A3	5.300	5.100	0.209	0.201
B	16.200	15.400	0.638	0.606
C	4.680	4.280	0.184	0.169
C1	1.500	1.100	0.059	0.043
D	1.000	0.600	0.039	0.024
E	3.800	3.400	0.150	0.134
G	9.300	8.700	0.366	0.343
H	0.600	0.400	0.024	0.016
K	2.700	2.100	0.106	0.083
L	13.600	12.800	0.535	0.504
M	1.500	1.100	0.059	0.043
N	2.590	2.490	0.102	0.098
T	W0.35		W0.014	
DIA	Φ1.5 TYP.	deep0.2 TYP.	Φ0.059 TYP.	deep0.008 TYP.